

II. AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions, and listings, of claims of the application.

1. (Currently Amended) A vertical PNP transistor and vertical NPN transistor comprising:
an emitter region of the vertical PNP transistor including silicon and germanium; and
an extrinsic base region of the vertical NPN transistor and an intrinsic base region of the vertical NPN transistor located in the same layer as the emitter region of the vertical PNP transistor,

wherein the same layer is polysilicon in the emitter region of the PNP transistor, and mono-crystal silicon in a portion of the extrinsic base region and mono-crystal silicon in the intrinsic base region of the NPN transistor.

2. (Original) The transistor of claim 1, wherein the germanium makes up no less than 10% of the silicon and germanium, and wherein the germanium makes up no more than 30% of the silicon and germanium.
3. (Cancelled)
4. (Original) The transistor of claim 1, wherein the transistor has a cutoff frequency greater than 1 GHz.
5. (Original) The transistor of claim 1, wherein the emitter region also includes carbon.

6. (Currently Amended) A vertical PNP and NPN transistor comprising:
a single layer of silicon that forms an emitter region of the PNP transistor, an extrinsic base region of the NPN transistor and an intrinsic base region of the NPN transistor,
wherein the single layer is polysilicon and includes germanium in the emitter region of the PNP transistor, and mono-crystal silicon in a portion of the extrinsic base region and mono-crystal silicon in the intrinsic base region of the NPN transistor.
7. (Cancelled)
8. (Currently Amended) The vertical PNP and NPN transistor of claim 7 6, wherein the germanium makes up no less than 10% of the silicon and germanium, and wherein the germanium makes up no more than 30% of the silicon and germanium.
9. (Currently Amended) The vertical PNP and NPN transistor of claim 7 6, wherein the emitter region also includes carbon.
10. (Cancelled)
11. (Previously Presented) The vertical PNP and NPN transistor of claim 6, wherein the PNP transistor has a cutoff frequency greater than 1 GHz.

12-20. (Previously Cancelled)